

2SB596

SILICON PNP TRIPLE DIFFUSED TYPE (PCT PROCESS)

POWER AMPLIFIER APPLICATIONS.

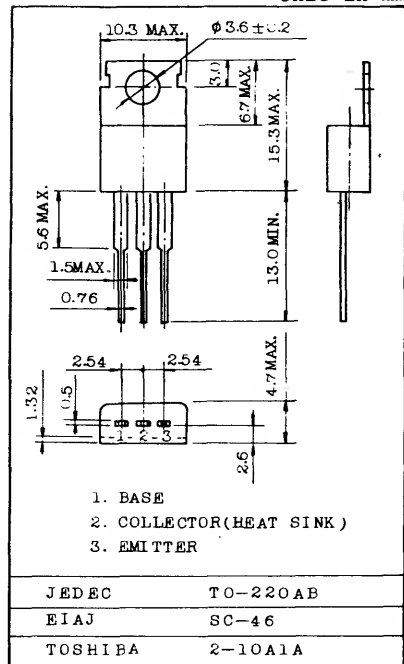
FEATURES:

- Good Linearity of h_{FE} .
- Complementary to 2SD526.
- Recommended for 20 ~ 25W High-Fidelity Audio Frequency Amplifier Output Stage.

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CB0}	-80	V
Collector-Emitter Voltage	V_{CEO}	-80	V
Emitter-Base Voltage	V_{EB0}	-5	V
Collector Current	I_C	-4	A
Emitter Current	I_E	4	A
Base Current	I_B	-3	A
Collector Power Dissipation ($T_c=25^\circ\text{C}$)	P_C	30	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$

Unit in mm



Mounting Kit No. AC75
Weight : 1.9g

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=-80\text{V}, I_E=0$	-	-	-30	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$	-	-	-100	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-50\text{mA}, I_B=0$	-80	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=-10\text{mA}, I_C=0$	-5	-	-	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE}=-5\text{V}, I_C=-0.5\text{A}$	40	-	240	
	$h_{FE(2)}$	$V_{CE}=-5\text{V}, I_C=-3\text{A}$	15	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-3\text{A}, I_B=-0.3\text{A}$	-	-1.0	-1.7	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=-5\text{V}, I_C=-3\text{A}$	-	-1.0	-1.5	V
Transition Frequency	f_T	$V_{CE}=-5\text{V}, I_C=-0.5\text{A}$	3	-	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=1\text{ MHz}$	-	130	-	pF

Note : $h_{FE(1)}$ Classification R : 40 ~ 80, O : 70 ~ 140, Y : 120 ~ 240

